

Unisys

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SUBJECT: Radiation Report on: SD5000B
Project: EOS-AM
Job #: M78301
Project part #: SD5000B

PPM-97-046

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A radiation evaluation was performed on SD5000B (TO-8 can) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a Co⁶⁰ gamma ray source. During the radiation testing, five parts were irradiated under bias (see Figure 1 for bias configuration) and one part was used as a control sample. The total dose radiation levels were 2.5, 5.0, 6.0, and 7.5 kRads.* The dose rate was between 0.025 and 0.062 kRads/hour (0.007 to 0.017 Rads/s). See Table II for the radiation schedule and effective dose rate calculation. After the 5.0 kRad exposure, the parts were annealed for 168 hours at 25°C. After the 7.5 kRad exposure, the parts were annealed for 216 hours at 25°C. After each radiation exposure and annealing treatment, parts were electrically tested according to the test conditions and the specification limits** listed in Table III.

Initial electrical measurements were made on 7 samples. Five samples (SN's 1, 3, 4, 9, and 12) were used as radiation samples while SN's 5 and 10 were used as a control samples.

All parts fell below the specification limit of -0.43V for dVGS with readings in the range of -0.88 to -0.92V. All parts passed all other tests during initial electrical measurements.

After the 2.5 kRad irradiation, all parts fell below the specification limit for dVGS with readings in the range of -0.82 to -0.88V. **All parts passed all other tests.**

After the 5.0 kRad irradiation, all parts failed VGSth with readings of 0.002V. The specification limit is 0.1V. All parts continued to fall below the specification limit for dVGS with readings in the range of -0.68 to -0.78V. **All parts passed all other tests.**

After the annealing the parts for 168 hours at 25°C, some parts showed some recovery in VGSth with two parts passing and three failing. Readings were in the range of 0.002 to 0.18V. All parts continued to fall below the specification limit for dVGS with readings in the range of -0.66 to -0.74V. **All parts passed all other tests.**

After the 6.0 kRad irradiation, two parts continued to pass VGSth with readings in the range of 0.002 to 0.18V. All parts continued to fall below the specification limit for dVGS with readings in the range of -0.64 to -0.74V. **All parts passed all other tests.**

* The term Rads, as used in this document, means Rads (silicon). All radiation levels cited are cumulative.

** These are manufacturer's pre-irradiation data specification limits. The manufacturer provided no post-irradiation limits at the time these tests were performed.

After the 7.5 kRad irradiation, all parts failed VGSth with readings of 0.002V. All parts continued to fall below the specification limit for dVGS with readings in the range of -0.62 to -0.64 V. **All parts passed all other tests.**

After the annealing the parts for 216 hours at 25°C, parts showed some recovery with two parts passing VGSth, one falling marginally below the specification limit and two with readings of 0.002V. All parts continued to fall below the specification limit for dVGS as before.

Table IV provides a summary of the test results with the mean and standard deviation values for each parameter after each irradiation exposure and annealing step.

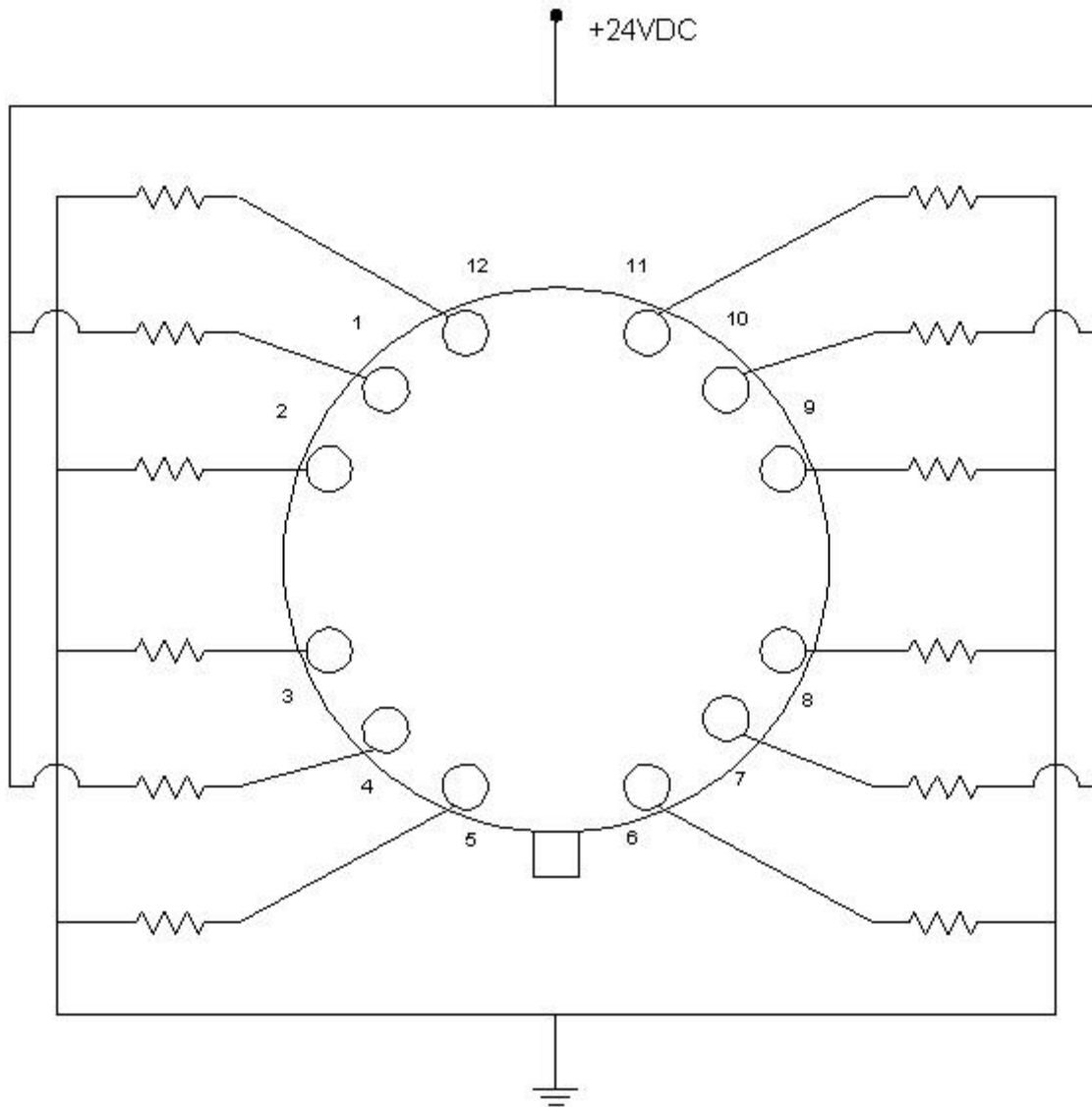
Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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Figure 1. Radiation Bias Circuit for SD5000B



Pin Connections:

1 G₁ 2 S₁ 3 S₂ 4 G₂ 5 D₂ 6 D₃ 7 G₃ 8 S₃ 9 S₄ 10 G₄ 11 D₄ 12 D₁

Notes:

1. Resistors are $47\text{k}\Omega \pm 5\%$, $\frac{1}{4}$ W.
2. $V_G = 24.0\text{V} \pm 0.5\text{V DC}$

TABLE I. Part Information

Generic Part Number:	SD5000B
EOS-AM Part Number	SD5000B
Charge Number:	M78301
Manufacturer:	Cal-Logic
Lot Date Code (LDC):	93-2629W#1
Quantity Tested:	7
Serial Number of Control Samples:	5, 10
Serial Numbers of Radiation Samples:	1, 3, 4, 9, and 12
Part Function:	High-Speed DMOS Quad
Part Technology:	Hybrid
Package Style:	TO-8 Can
Test Equipment:	Testronics
Test Engineer:	B. Chong

- The manufacturer for this part guaranteed no radiation tolerance/hardness.

